

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1819 is a switching device that can be driven directly by a 4.0 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power management of notebook computers and so on.

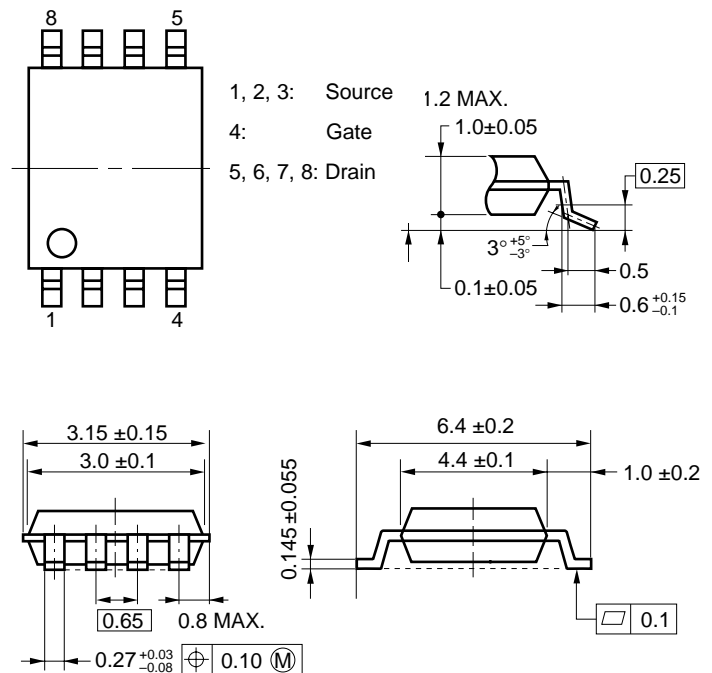
FEATURES

- 4.0 V drive available
- Low on-state resistance
 - $R_{DS(on)1} = 12 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -10 \text{ V}$, $I_D = -6.0 \text{ A}$)
 - $R_{DS(on)2} = 18.5 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -4.5 \text{ V}$, $I_D = -6.0 \text{ A}$)
 - $R_{DS(on)3} = 22 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -4.0 \text{ V}$, $I_D = -6.0 \text{ A}$)
- Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1819GR-9JG	Power TSSOP8

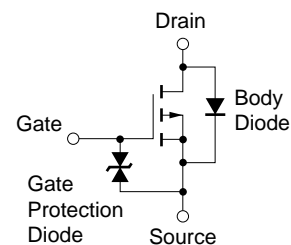
PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{bss}	-30	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_A = 25^\circ\text{C}$)	$I_{D(DC)}$	± 12	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 48	A
Total Power Dissipation ^{Note2}	P_T	2.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

EQUIVALENT CIRCUIT



- Notes 1.** $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$
- 2.** Mounted on ceramic substrate of $5000 \text{ mm}^2 \times 1.1 \text{ mm}$

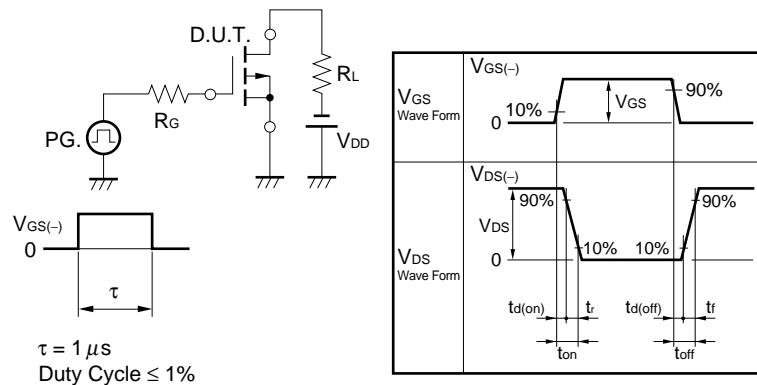
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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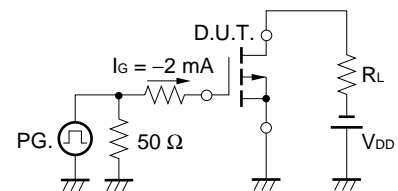
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V			-1.0	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1.0 mA	-1.0	-2.0	-2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -6.0 A	11	23		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -10 V, I _D = -6.0 A		9.8	12	mΩ
	R _{DS(on)2}	V _{GS} = -4.5 V, I _D = -6.0 A		13.9	18.5	mΩ
	R _{DS(on)3}	V _{GS} = -4.0 V, I _D = -6.0 A		16.4	22	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		2430		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		690		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz		420		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -15 V, I _D = -6.0 A		19		ns
Rise Time	t _r	V _{GS} = -10 V		17		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		160		ns
Fall Time	t _f			160		ns
Total Gate Charge	Q _G	V _{DD} = -24 V		45		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -10 V		5.5		nC
Gate to Drain Charge	Q _{GD}	I _D = -12 A		15		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 12 A, V _{GS} = 0 V		0.83		V
Reverse Recovery Time	t _{rr}	I _F = 12 A, V _{GS} = 0 V		50		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		40		nC

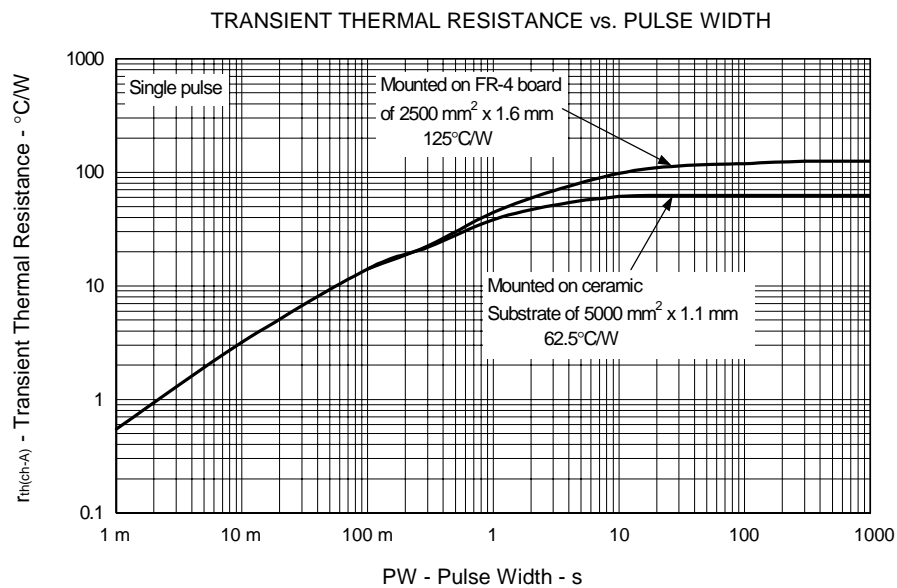
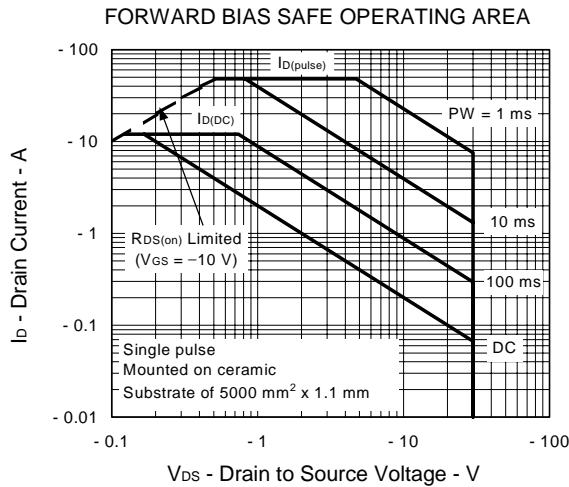
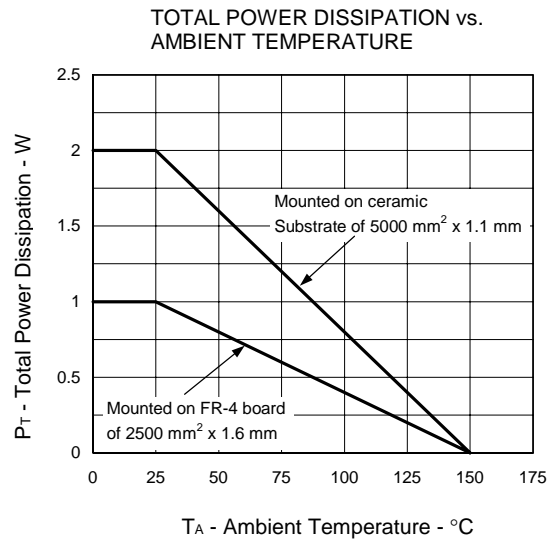
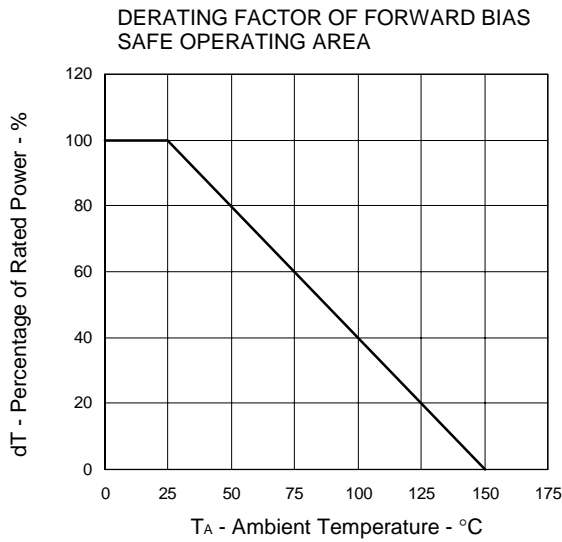
TEST CIRCUIT 1 SWITCHING TIME



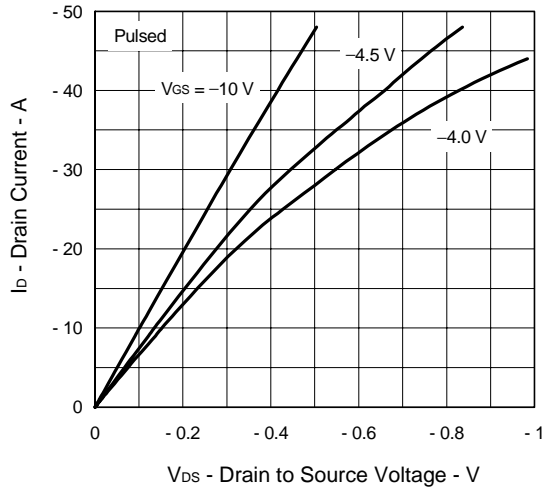
TEST CIRCUIT 2 GATE CHARGE



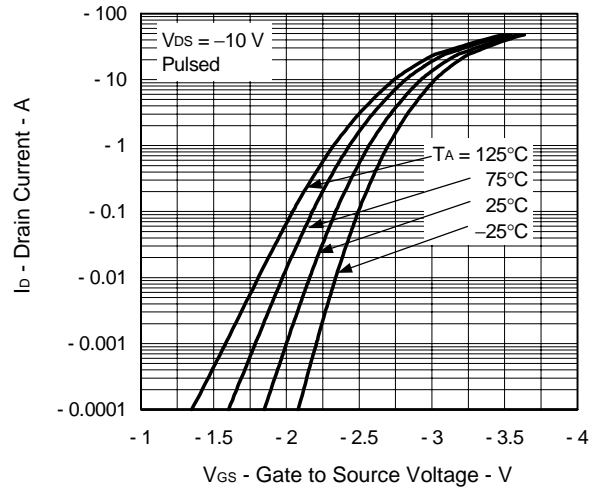
TYPICAL CHARACTERISTICS (T_A = 25°C)



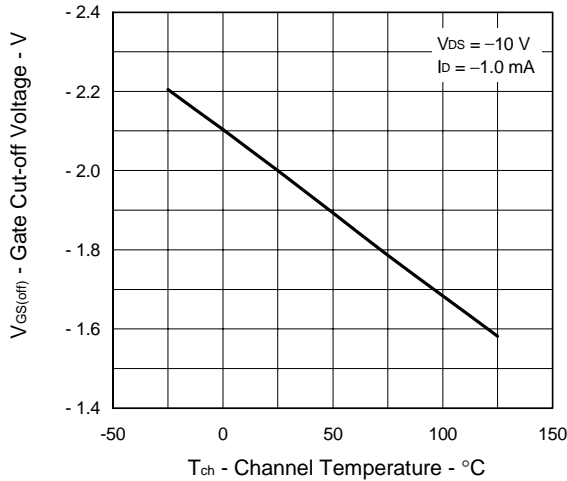
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



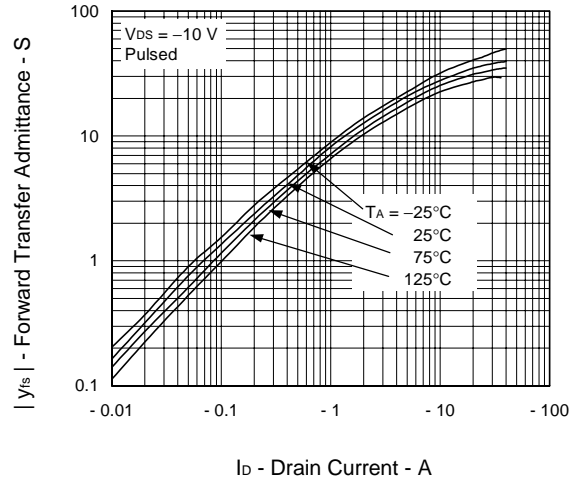
FORWARD TRANSFER CHARACTERISTICS



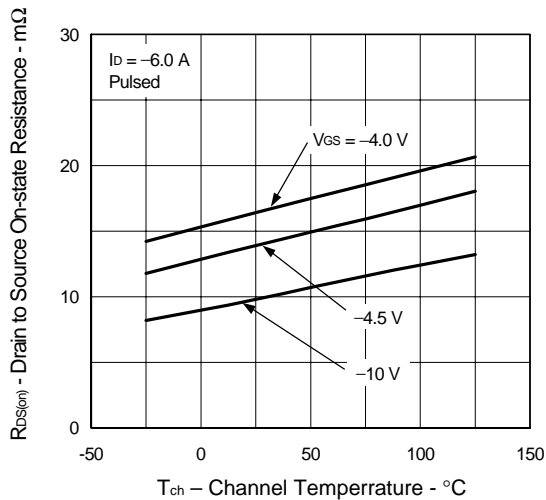
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



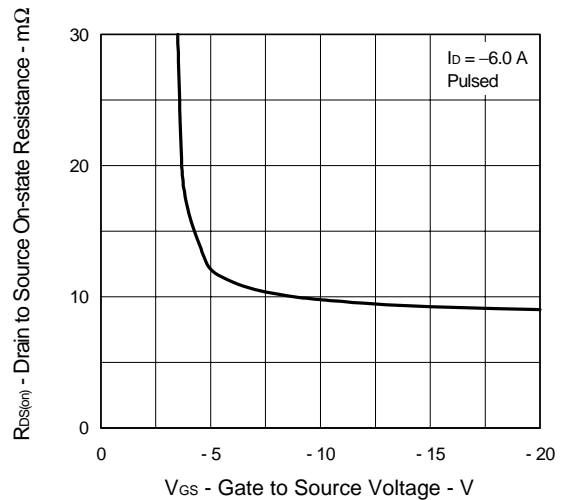
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



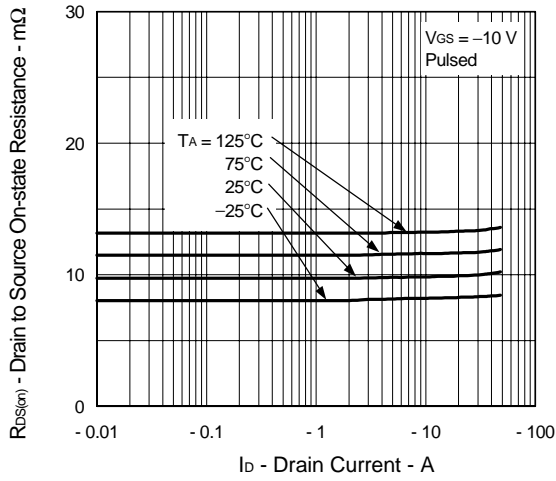
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



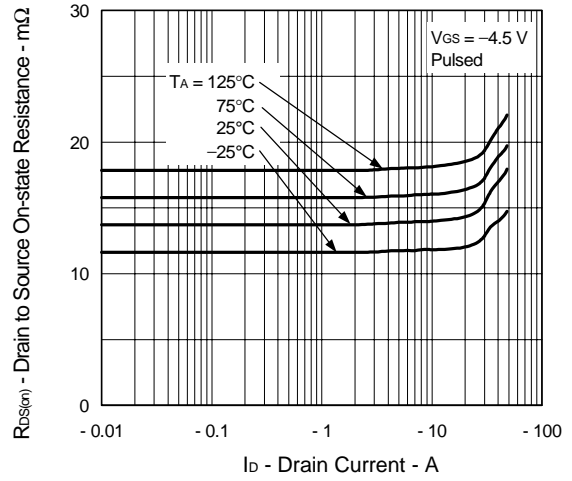
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



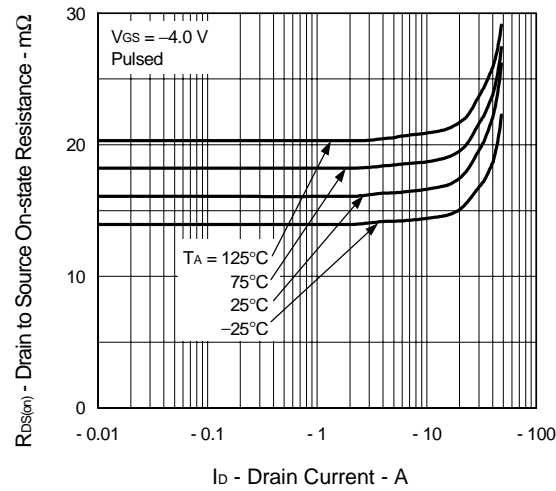
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



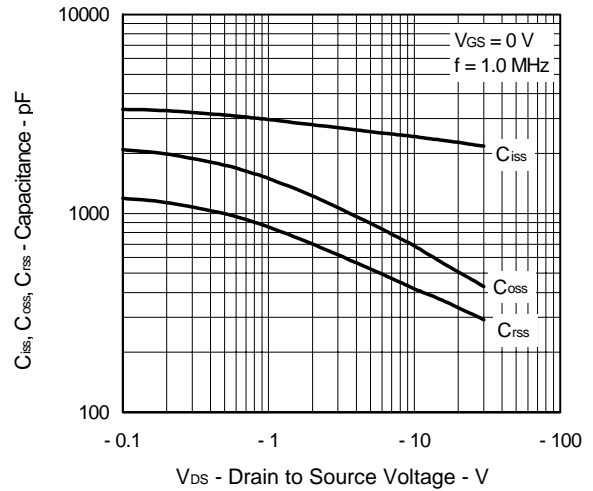
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



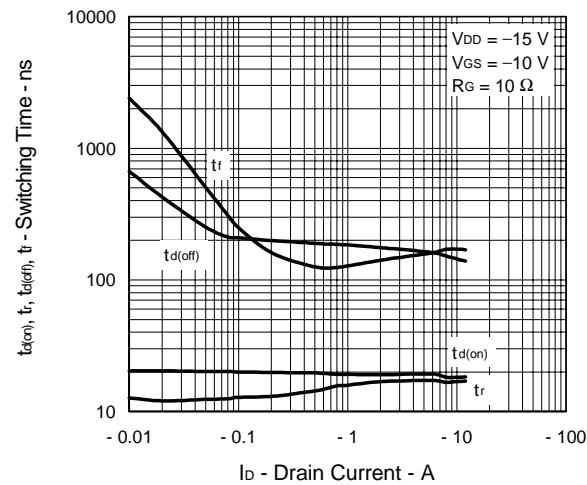
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



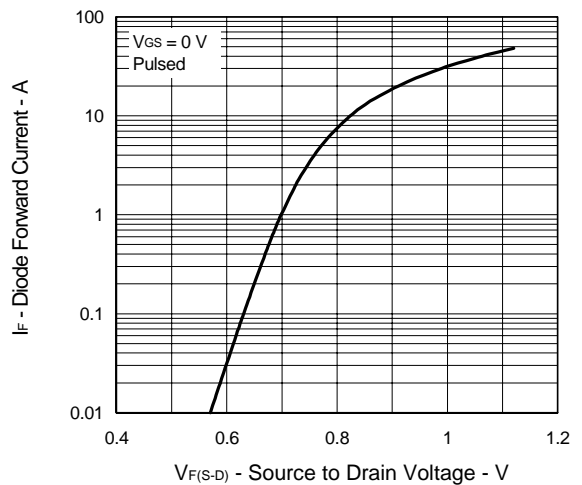
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



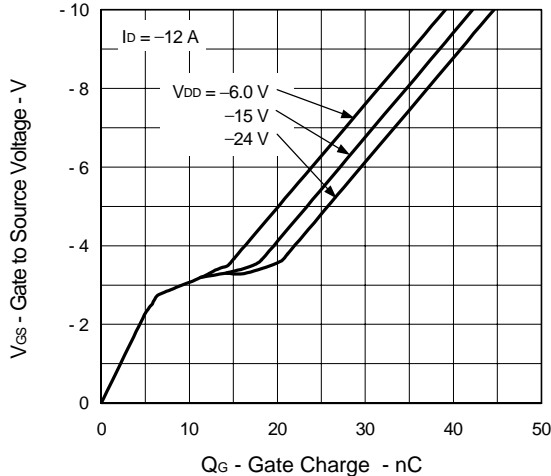
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



[MEMO]

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